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INFORMATION DISCLOSURE STATEMENT BY APPLICANT (use as many sheets as necessary)				Complete If Known	
Application Number	10/091,338				
Filing Date	March 6, 2002				
First Named Inventor	Toru MITSUKI et al.				
Group Art Unit	2824				
Examiner Name	Bradley Smith				
Attorney Docket Number	0756-2448				
Sheet	1	of	1		

U.S. PATENT DOCUMENTS						
Examiner Initials*	Cite No. <sup>1</sup>	U.S. Patent Document		Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number	Kind Code <sup>2</sup> (if known)			

FOREIGN PATENT DOCUMENTS								
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		Office <sup>3</sup>	Number <sup>4</sup>	Kind Code <sup>2</sup> (if known)				
BKS ↓ ✓		JP	07-162004			06/23/1995		AB
		WO	93-10555			05/27/1993		AB
		JP	04-035021			02/05/1992		AB
		JP	04-286336			10/12/1992		AB

OTHER PRIOR ART - NON PATENT LITERATURE DOCUMENTS			
Examiner Initials*	Cite No. <sup>1</sup>	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T <sup>2</sup>
BS		H. Koseki et al., <i>Recent Progress of Low Temperature Poly-Si Technology</i> , Electronic Display Forum, Pages 4-31 to 4-38 and English Translation, Pages 1-21, April 15, 1999.	
BS		Kenji Sera et al., <i>Uniformity Improvement of Excimer Laser Crystallized Poly-Si Thin Film Transistors</i> , AM-LCD '96/IDM '96, Pages 85-88.	
BS		M. Bonnel et al., <i>Polycrystalline Silicon Thin-Film Transistors with Two-Step Annealing Process</i> , IEEE Electron Device Letters, Vol. 14, No. 12, Pages 551-553, December 1993.	
BS		M. Fuse et al., <i>Performance of Poly-Si Thin Film Transistors Fabricated by Excimer- Laser Annealing of SiH<sub>4</sub> and Si<sub>2</sub>H<sub>6</sub> Source Low Pressure Vapor Deposited <math>\alpha</math>-Si Films With or Without Solid-Phase Crystallization</i> , Solid State Phenomena, Vols. 37-38, Pages 565-570, 1994.	

Examiner Signature	<i>BS</i>	Date Considered	6/15/04
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